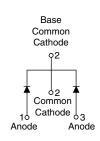


HALOGEN

FREE

Hyperfast Rectifier, 30 A FRED Pt®





PRIMARY CHARACTERISTICS							
Package	D ² PAK (TO-263AB)						
I _{F(AV)}	2 x 15 A						
V_{R}	200 V						
V _F at I _F	0.78 V						
t _{rr} typ.	30 ns						
T _J max.	175 °C						
Circuit configuration	Common cathode						

FEATURES

- · Hyperfast recovery time
- Low forward voltage drop
- · Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- · AEC-Q101 qualified, class 1 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Vishay Semiconductors 200 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

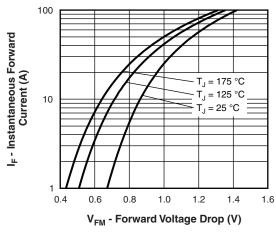
ABSOLUTE MAXIMUM RATINGS									
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS				
Peak repetitive reverse voltage		V_{RRM}		200	V				
Average rectified forward current	per diode	I _E (Δ\Λ	T _C = 159 °C	15					
	per device			30	Α				
Non-repetitive peak surge current		I _{FSM}	T _C = 25 °C	200					
Operating junction and storage ten	T _J , T _{Stg}		-55 to +175	°C					

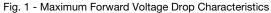
ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	200	-	-	V				
Forward voltage	V _F	I _F = 15 A	-	0.92	1.05	V				
		I _F = 15 A, T _J = 125 °C	-	0.78	0.85	V				
Davaga laakaga ayuunt	alsaga ayyyyant	$V_R = V_R$ rated	-	-	10					
Reverse leakage current	I _R	$T_J = 125 ^{\circ}C$, $V_R = V_R$ rated	-	5	300	μΑ				
Junction capacitance	C _T	V _R = 200 V	-	57	-	pF				
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH				



DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS				
		$I_F = 1 A, dI_F/dt = 1$	00 A/μs, V _R = 30 V	-	-	30				
Reverse recovery time	t _{rr}	T _J = 25 °C	- I _F = 15 A	26	-	ns				
		T _J = 125 °C		-	40	-				
Dook wasayam ayamant	I _{RRM}	T _J = 25 °C		-	2.8	-	A			
Peak recovery current		T _J = 125 °C		-	6.0	-				
Reverse recovery charge	0	T _J = 25 °C	- 37	-						
	Q_{rr}	T _J = 125 °C		=	120	=	nC			

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}	-55	-	175	°C				
Thermal resistance, junction to case per diode	R _{thJC}	-	-	1.1	°C/W				
Matala		-	2.0	-	g				
Weight		-	0.07	-	oz.				
Mounting torque		6.0	_	12	kgf ⋅ cm				
Woulding torque		(5.0)		(10)	(lbf ⋅ in)				
Marking device		Case style D ² P/	AK (TO-263AB)	AB) 30CTH02SH					





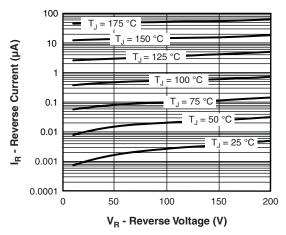


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

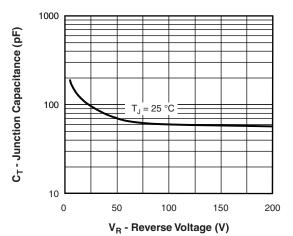


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

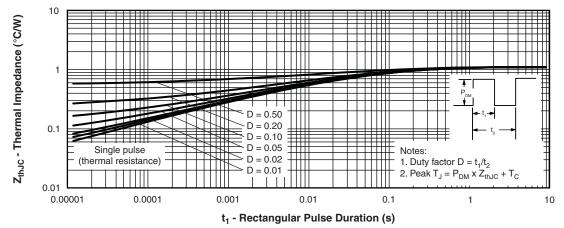


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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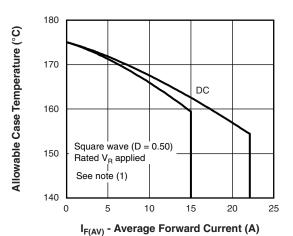


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

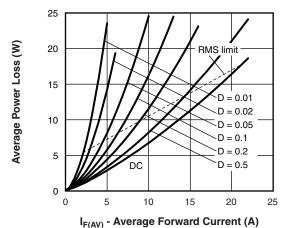


Fig. 6 - Forward Power Loss Characteristics

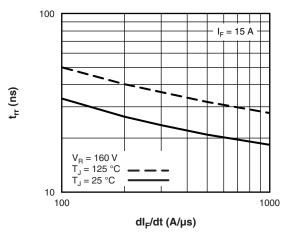


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

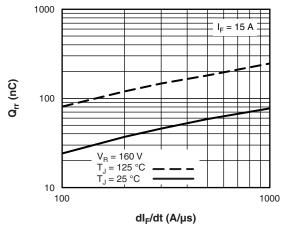
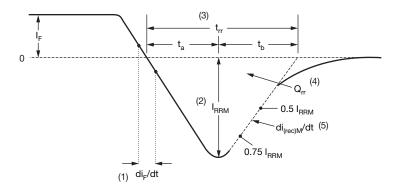


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $^{(1)}$ Formula used: T_C = T_J - (Pd + Pd_{REV}) x R_{thJC}; Pd = forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 6); Pd_{REV} = inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = rated V_R

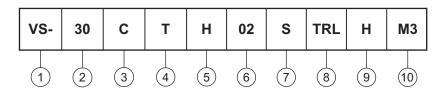


- (1) di_F/dt rate of change of current through zero crossing
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}
- (2) I_{RRM} peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (5) $di_{(rec)M}/dt$ peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



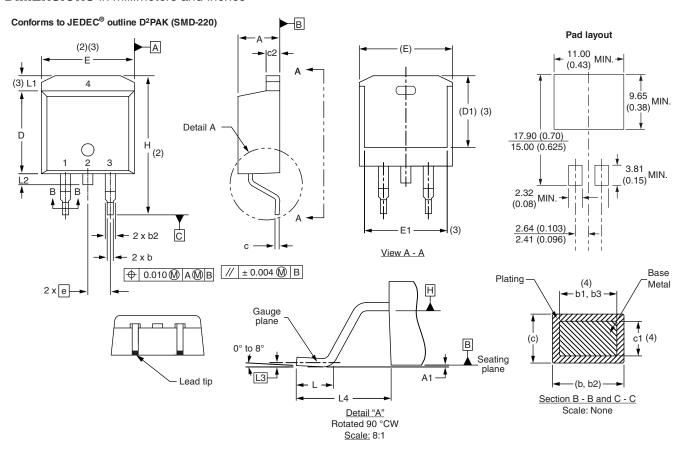
- 1 Vishay Semiconductors product
- 2 Current rating (30 A)
- 3 C = common cathode
- 4 T = TO-220, D²PAK
- 5 H = hyperfast rectifier
- 6 Voltage rating (02 = 200 V)
- None = tube (50 pieces)
 - TRL = tape and reel (left oriented, for D²PAK package)
 - TRR = tape and reel (right oriented, for D²PAK package)
- 9 H = AEC-Q101 qualified
- 10 M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

LINKS TO RELATED DOCUMENTS							
Dimensions <u>www.vishay.com/doc?95046</u>							
Part marking information	www.vishay.com/doc?95444						
Packaging information	www.vishay.com/doc?95032						



D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	ETERS	INC	HES	NOTES		SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	e 2.54 BSC 0.100 BSC) BSC		
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



Vishay

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